

Title (en)

METHOD FOR THE PRODUCTION OF LAYERS OF RERAM MEMORIES, AND USE OF AN IMPLANTATION DEVICE

Title (de)

VERFAHREN ZUR HERSTELLUNG VON SCHICHTEN VON ReRAM-SPEICHERN UND VERWENDUNG EINES IMPLANTERS

Title (fr)

PROCÉDÉ DE PRODUCTION DE COUCHES DE MÉMOIRES RERAM ET UTILISATION D'UN IMPLANTEUR IONIQUE

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Application

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Abstract (en)

[origin: WO2017190719A1] The invention relates to a method for producing layers of ReRAM memories and the use of an implantation device. According to the invention, in order to produce ReRAM memories, TMO layers are applied to an electrode in a desired sequence, a process during which at least one TMO layer is bombarded with ions, e.g. oxygen ions, by means of an ion implantation device such that ions are imported into said TMO layer.

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Citation (search report)

See references of WO 2017190719A1

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